

Atomic-scale characterization of plasma-induced damage in plasma-enhanced atomic layer deposition

Kangsik Kim^a, Il-Kwon Oh^b, Hyungjun Kim^b and Zonghoon Lee^{a*}

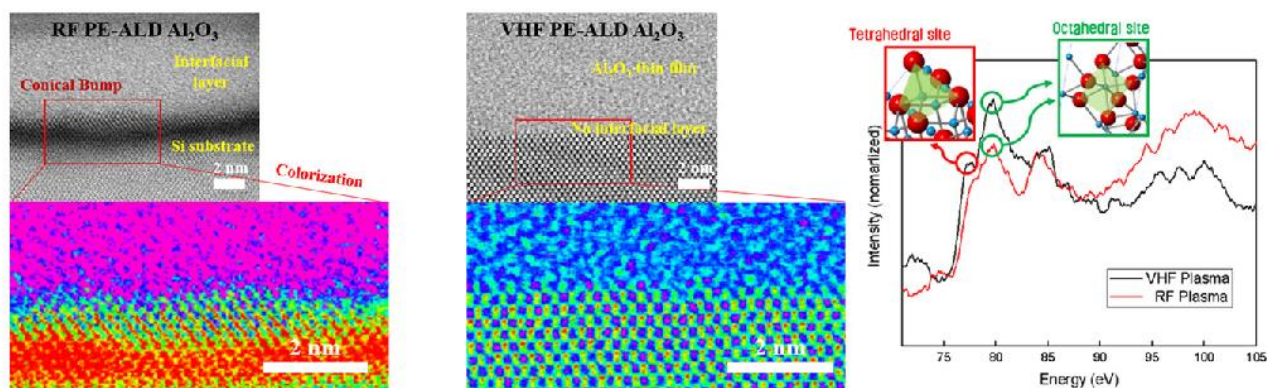
^aSchool of Materials Science and Engineering, Ulsan National Institute of Science and Technology (UNIST), Ulsan 44919, Republic of Korea

^bSchool of Electrical and Electronic Engineering, Yonsei University, Seoul 03722, Republic of Korea

* Corresponding Author

E-mail address: zhlee@unist.ac.kr (Z. Lee)

Graphical abstract



Highlights

- Deposition process of VHF PE-ALD shows a reduction of the plasma-induced damage.
- VHF plasma technology can control atomic configuration on the surface.
- Increasing number of reactive ions and radicals has an influence on film formation.
- Dielectric constant of amorphous Al_2O_3 is related to lattice dielectric constant.

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